

**Features**

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Green Device Available

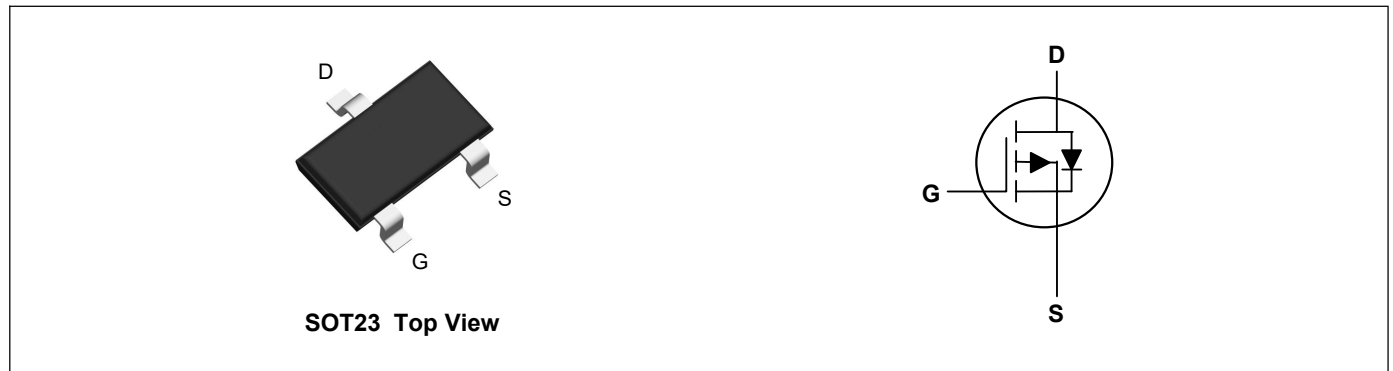
**Product Summary**



$V_{DS}$	-60	V
$I_D$	-1.6	A
$R_{DS(ON)}$ (at $V_{GS}=-10V$ )	190	m $\Omega$
$R_{DS(ON)}$ (at $V_{GS}=-4.5V$ )	210	m $\Omega$

**Applications**

- High Frequency Point-of-Load, Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch



**Absolute Maximum Ratings ( $T_A=25^{\circ}C$ , unless otherwise noted)**

Parameter	Symbol	Rating	Units
Drain-Source Voltage	$V_{DS}$	-60	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current	$I_D@T_A=25^{\circ}C$	-1.6	A
Continuous Drain Current	$I_D@T_A=70^{\circ}C$	-1.2	A
Pulsed Drain Current <sup>2</sup>	$I_{DM}$	-8	A
Total Power Dissipation <sup>3</sup>	$P_D@T_A=25^{\circ}C$	1.5	W
Total Power Dissipation <sup>3</sup>	$P_D@T_A=70^{\circ}C$	1.4	W
Storage Temperature Range	$T_{STG}$	-55 to 150	$^{\circ}C$
Operating Junction Temperature Range	$T_J$	-55 to 150	$^{\circ}C$

**Thermal Characteristics**

Parameter	Symbol	Typ	Max	Unit
Thermal Resistance Junction-Ambient <sup>1</sup> ( $t \leq 10S$ )	$R_{\theta JA}$	---	80	$^{\circ}C/W$
Thermal Resistance Junction-Ambient <sup>1</sup>		---	83	$^{\circ}C/W$

**Electrical Characteristics (T<sub>J</sub>=25°C, unless otherwise noted)**

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =-250uA	-60	---	---	V
Static Drain-Source On-Resistance <sup>2</sup>	R <sub>DS(ON)</sub>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-1.5A	---	140	190	mΩ
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-1.5A	---	160	210	mΩ
		V <sub>GS</sub> =-2.5V, I <sub>D</sub> =-1A	---	180	240	mΩ
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =-250uA	-1.4	---	-2.6	V
Drain-Source Leakage Current	I <sub>DSS</sub>	V <sub>DS</sub> =-60V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	---	-1	uA
		V <sub>DS</sub> =-60V, V <sub>GS</sub> =0V, T <sub>J</sub> =55°C	---	---	-5	
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	---	---	±100	nA
Forward Transconductance	g <sub>fs</sub>	V <sub>DS</sub> =-5V, I <sub>D</sub> =-1.5A	---	3	---	S
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =-30V, V <sub>GS</sub> =-10V, I <sub>D</sub> =-1.5A	---	14.3	---	nC
Gate-Source Charge	Q <sub>gs</sub>		---	2.2	---	
Gate-Drain Charge	Q <sub>gd</sub>		---	3.2	---	
Turn-On Delay Time	T <sub>d(on)</sub>	V <sub>DD</sub> =-30V, V <sub>GS</sub> =-10V, R <sub>G</sub> =3Ω, I <sub>D</sub> =-1.5A	---	40	---	ns
Rise Time	T <sub>r</sub>		---	35	---	
Turn-Off Delay Time	T <sub>d(off)</sub>		---	15	---	
Fall Time	T <sub>f</sub>		---	10	---	
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =-30V, V <sub>GS</sub> =0V, f=1MHz	---	370	---	pF
Output Capacitance	C <sub>oss</sub>		---	31.5	---	
Reverse Transfer Capacitance	C <sub>rss</sub>		---	5	---	

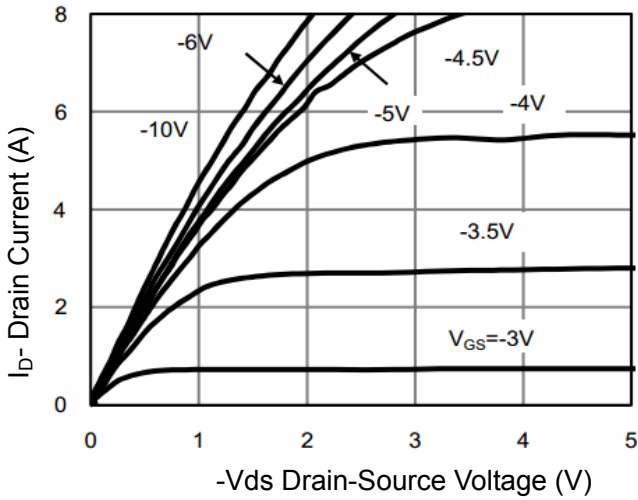
**Drain-Source Diode Characteristics**

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Continuous Source Current <sup>1,4</sup>	I <sub>S</sub>		---	---	-1.6	A
Diode Forward Voltage <sup>2</sup>	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =-1.5A, T <sub>J</sub> =25°C	---	---	-1.2	V
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> =-1.5A, di/dt=100A/μs, T <sub>J</sub> =25°C	---	25	---	nS
Reverse Recovery Charge	Q <sub>rr</sub>		---	31	---	nC

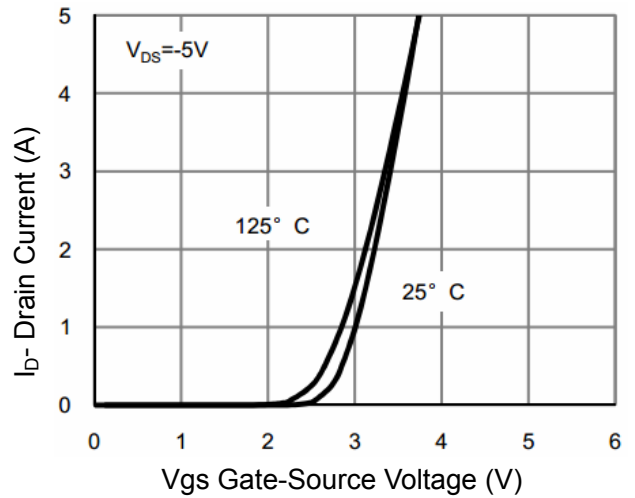
**Note:**

- 1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
- 2.The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
- 3.The power dissipation is limited by 150°C junction temperature
- 4.The data is theoretically the same as I<sub>D</sub> and I<sub>DM</sub>, in real applications, should be limited by total power dissipation.

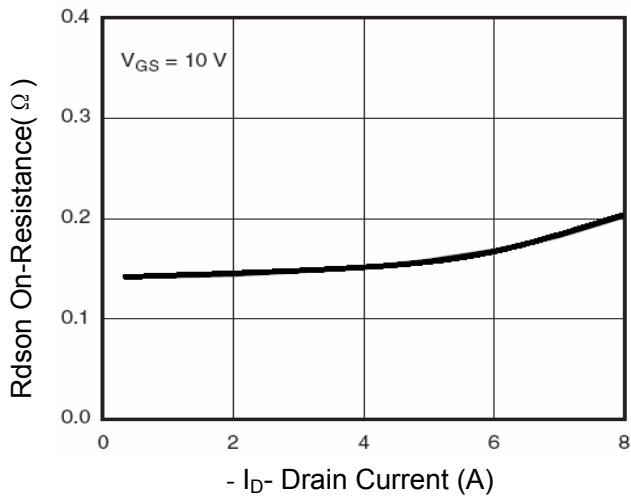
**Typical Characteristics**



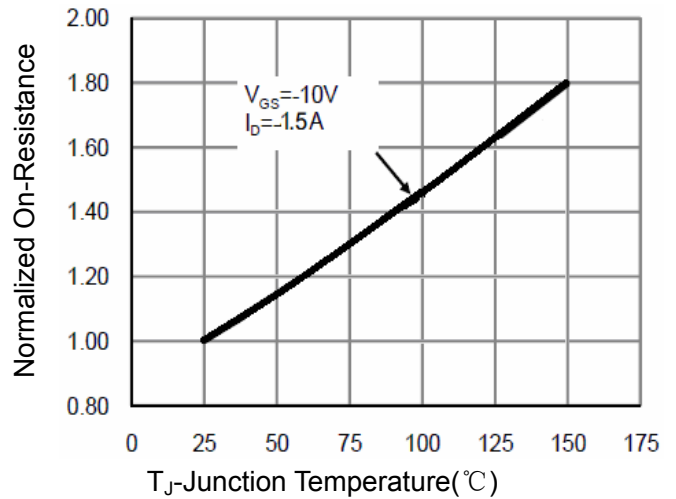
**Figure 1 Output Characteristics**



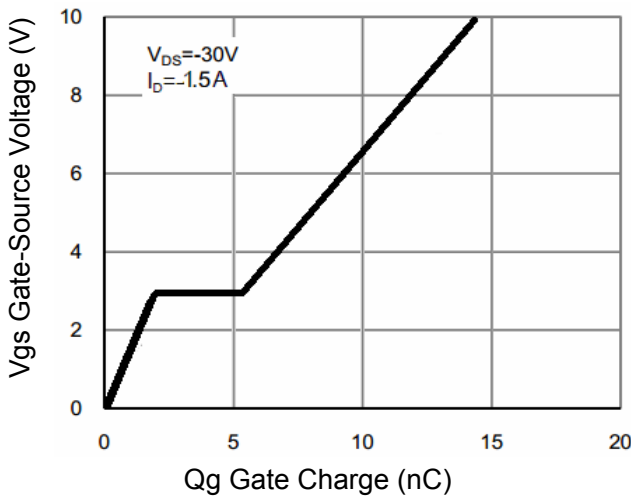
**Figure 2 Transfer Characteristics**



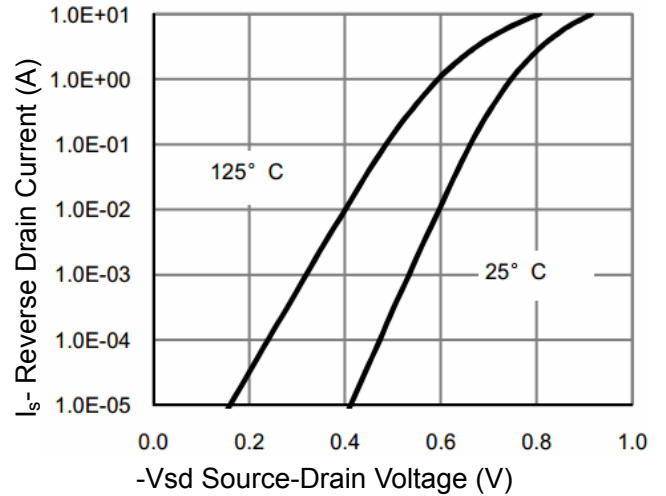
**Figure 3 Rdson- Drain Current**



**Figure 4 Rdson-Junction Temperature**



**Figure 5 Gate Charge**



**Figure 6 Source- Drain Diode Forward**

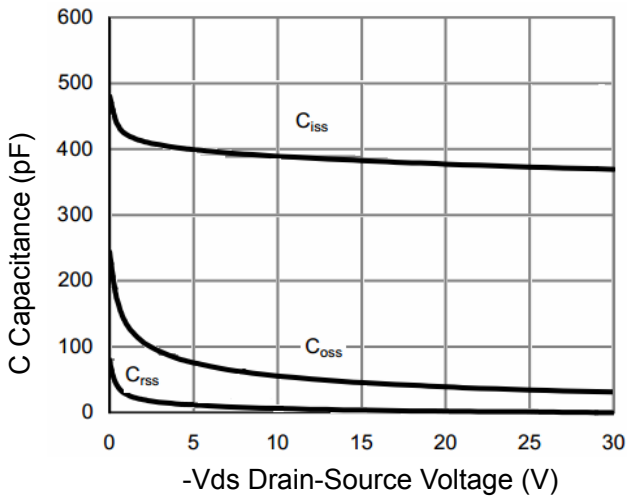


Figure 7 Capacitance vs Vds

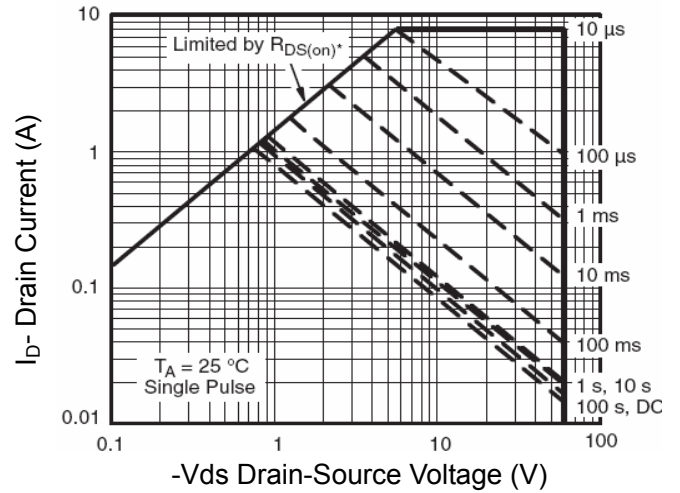


Figure 8 Safe Operation Area

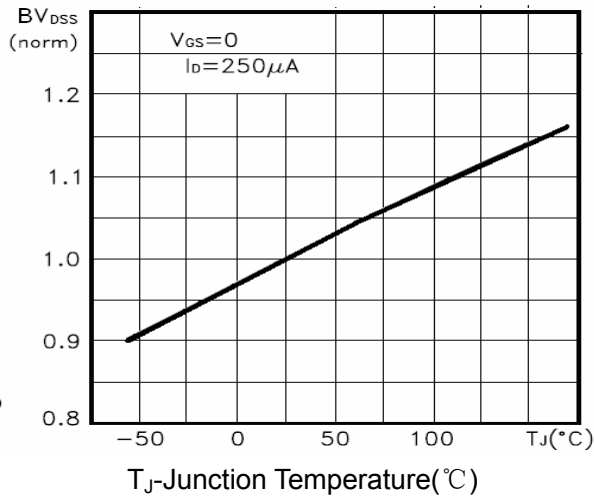


Figure 9  $BV_{DSS}$  vs Junction Temperature

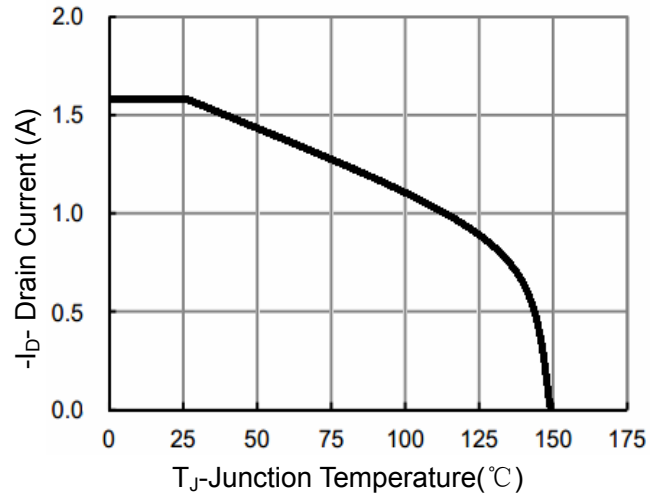


Figure 10  $I_D$  Current De-rating

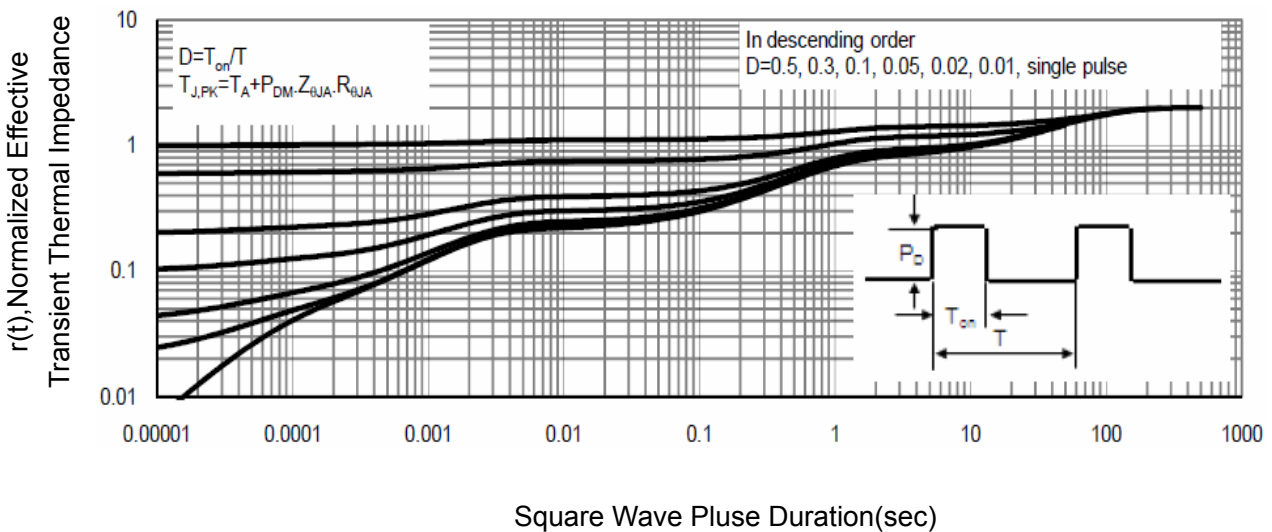
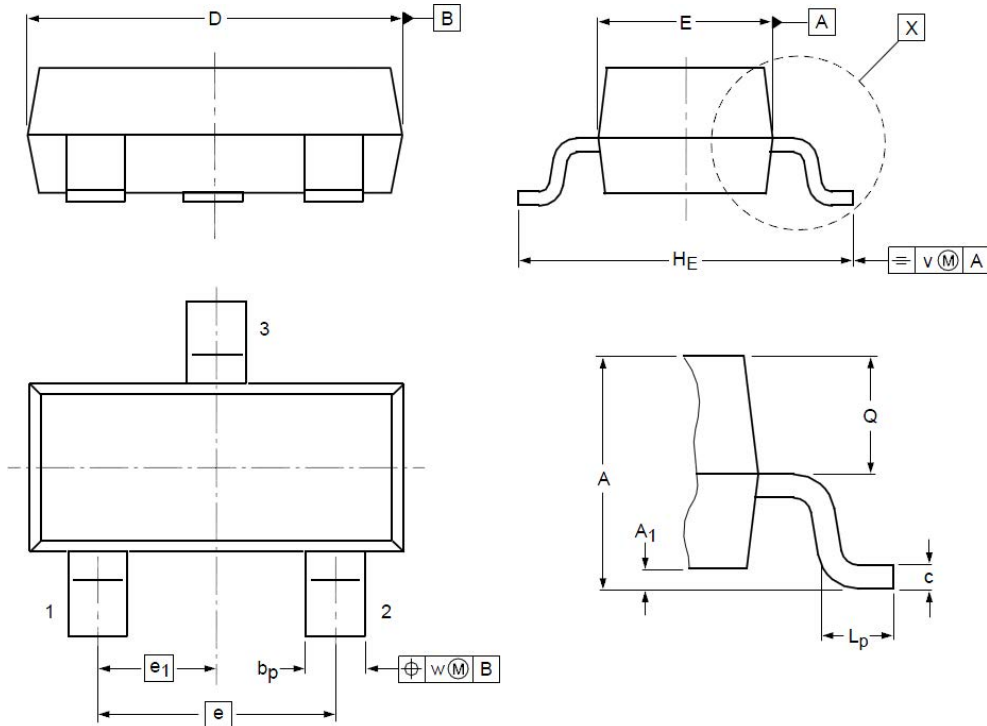


Figure 11 Normalized Maximum Transient Thermal Impedance

**SOT23 Package Outline Dimensions**



Symbol	Dimensions (unit:mm)			Symbol	Dimensions (unit:mm)		
	Min	Typ	Max		Min	Typ	Max
<b>A</b>	0.90	1.05	1.20	<b>e<sub>1</sub></b>	--	0.95	--
<b>A<sub>1</sub></b>	0.01	0.05	0.10	<b>H<sub>E</sub></b>	2.10	2.40	2.50
<b>b<sub>p</sub></b>	0.38	0.42	0.48	<b>L<sub>p</sub></b>	0.40	0.50	0.60
<b>c</b>	0.09	0.13	0.15	<b>Q</b>	0.45	0.49	0.55
<b>D</b>	2.80	2.92	3.00	<b>V</b>	--	0.20	--
<b>E</b>	1.20	1.33	1.40	<b>W</b>	--	0.10	--
<b>e</b>	--	1.90	--				